

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning on page 1, line 11, with the following amended paragraph:

---In late years, it has been proposed to construct an acceleration sensor or an angular velocity sensor as a micromachine using semiconductor manufacturing technologies. This type of micromachine requires a mass body having a relatively large inertial mass. As a method of forming such a mass body, it is conceivable to form a through-hole (including a slit-shaped through-hole) in a semiconductor substrate having a relatively large thickness dimension (several hundred μm) so as to separate a mass body from the remaining region. The through-hole is formed in a semiconductor substrate with a relatively large thickness dimension by means of an etching technique, such as a wet etching process or a reactive-ion etching process. This technique is disclosed, for example, in Sunil A. ~~Bhave~~ Bhave et al. "AN INTEGRATED VERTICAL-DRIVE, IN-PLANE-SENSE MICROGYROSCOPE", TRANSDUCERS '03 (IEEE, The 12th International Conference on Solid-State Sensor, Actuators and Microsystems), USA, June 8-12, 2003, p. 171.---